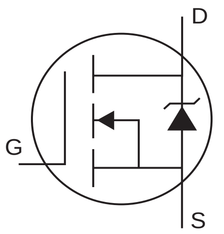
PD - 91305C

IRFZ46NS
IRFZ46NL

HEXFET® Power MOSFET

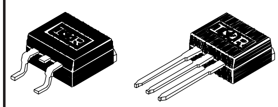
- Advanced Process Technology
- Surface Mount (IRFZ46NS)
- Low-profile through-hole (IRFZ46NL)
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated



V_{DSS} = 55V

$R_{DS(on)}$ = 0.0165Ω

I_D = 53A⑧



D²Pak TO-262

Description

Advanced HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D^2Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D^2Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.
The through-hole version (IRFZ46NL) is available for low-profile applications.

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V⑤	53 ⑧	
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V⑤	37	A
I_{DM}	Pulsed Drain Current ①⑤	180	
P_D @T_A = 25°C	Power Dissipation	3.8	W
P_D @T_C = 25°C	Power Dissipation	107	W
	Linear Derating Factor	0.71	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
I_{AR}	Avalanche Current①	28	A
E_{AR}	Repetitive Avalanche Energy①	11	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑤	5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

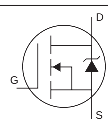
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	–––	1.4	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted,steady-state)**	–––	40	

04/08/04

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	–––	–––	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.057	–––	V/°C	Reference to 25°C, I_D =1mA⑤
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	–––	.0165	Ω	V_{GS} =10V, I_D = 28A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	–––	4.0	V	V_{DS} = V_{GS}, I_D = 250μA
g_{fs}	Forward Transconductance	19	–––	–––	S	V_{DS} = 25V, I_D = 28A④⑤
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	25	μA	V_{DS} = 55V, V_{GS} = 0V
		–––	–––	250		V_{DS} = 44V, V_{GS} = 0V, T_J = 150°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	–––	–––	-100		V_{GS} = -20V
Q_g	Total Gate Charge	–––	–––	72	nC	I_D = 28A
Q_{gs}	Gate-to-Source Charge	–––	–––	11		V_{DS} = 44V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	–––	26		V_{GS} = 10V, See Fig. 6 and 13 ④⑤
$t_{d(on)}$	Turn-On Delay Time	–––	14	–––	ns	V_{DD} = 28V
t_r	Rise Time	–––	76	–––		I_D = 28A
$t_{d(off)}$	Turn-Off Delay Time	–––	52	–––		R_G = 12Ω
t_f	Fall Time	–––	57	–––		R_D = 0.98Ω, See Fig. 10④⑤
L_S	Internal Source Inductance	–––	7.5	–––	nH	Between lead, and center of die contact
C_{iss}	Input Capacitance	–––	1696	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	407	–––		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	–––	110	–––		ƒ = 1.0MHz, See Fig. 5⑤
E_{AS}	Single Pulse Avalanche Energy ②	–––	583⑥	152⑦		I_{AS} = 28A, L = 389mH

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	53	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	180		
V_{SD}	Diode Forward Voltage	–––	–––	1.3	V	T_J = 25°C, I_S = 28A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	–––	67	101	ns	T_J = 25°C, I_F = 28A
Q_{rr}	Reverse Recovery Charge	–––	208	312	nC	di/dt = 100A/μs ④⑤
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 389μH R_G = 25Ω, I_{AS} = 28A. (See Figure 12)

③ $I_{SD} \le$ 28A, di/dt ≤ 220A/μs, $V_{DD} \le V_{(BR)DSS}$, $T_J \le$ 175°C.

④ Pulse width ≤ 400μs; duty cycle ≤ 2%.

⑤ Uses IRFZ46N data and test conditions.

⑥ This is a typical value at device destruction and represents operation outside rated limits.

⑦ This is a calculated value limited to TJ = 175°C.

⑧ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 39A.

** When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.

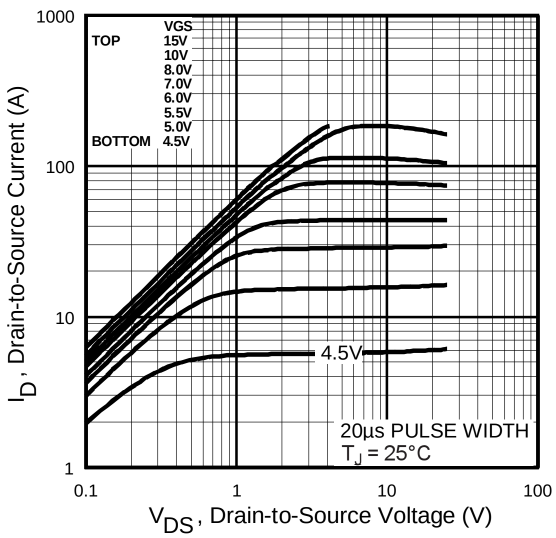


Fig 1. Typical Output Characteristics

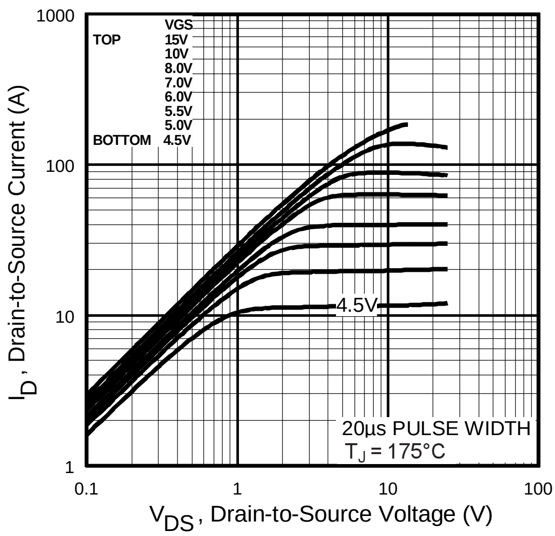


Fig 2. Typical Output Characteristics

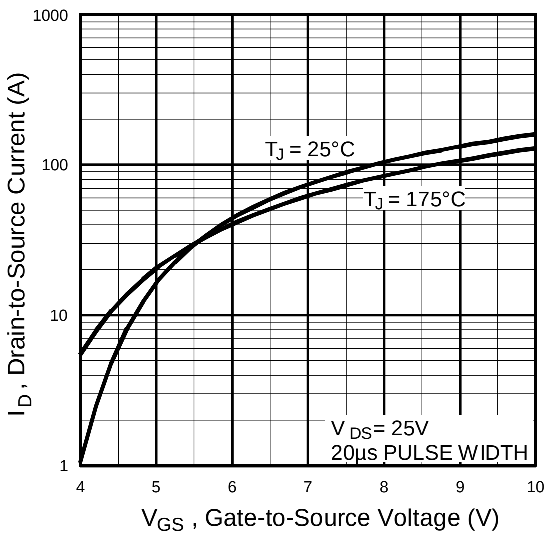


Fig 3. Typical Transfer Characteristics

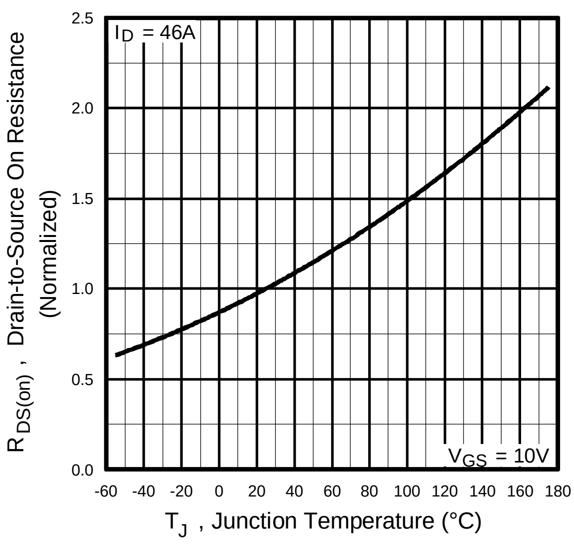


Fig 4. Normalized On-Resistance Vs. Temperature

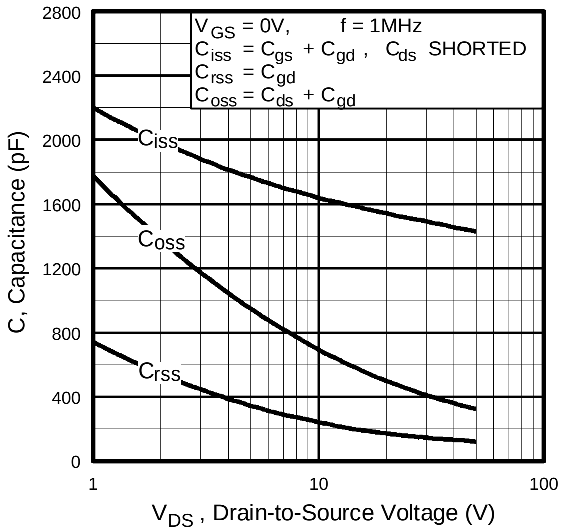


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

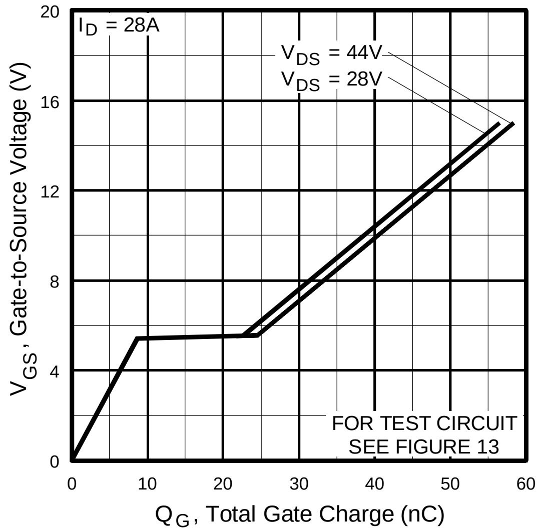


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

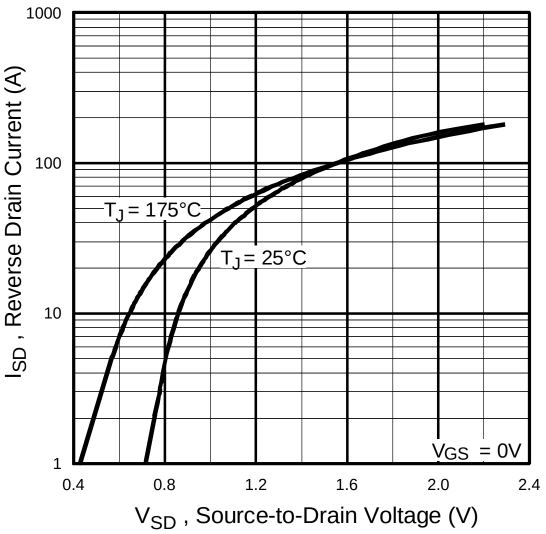


Fig 7. Typical Source-Drain Diode Forward Voltage

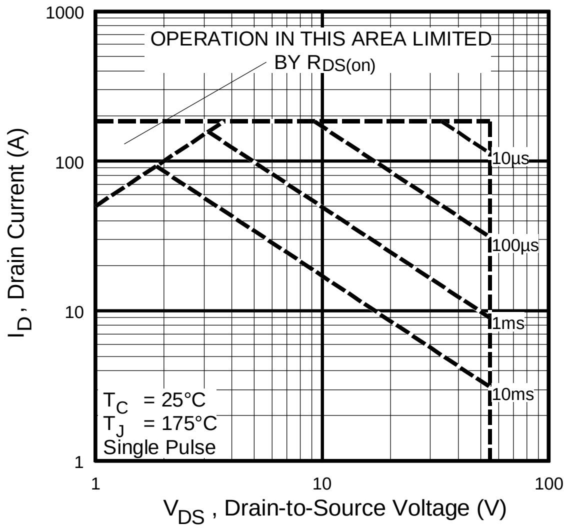


Fig 8. Maximum Safe Operating Area

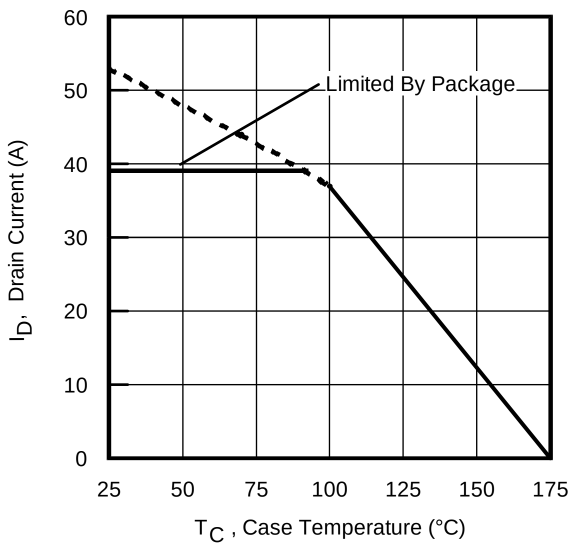


Fig 9. Maximum Drain Current Vs. Case Temperature

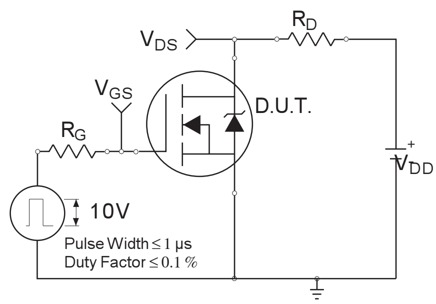


Fig 10a. Switching Time Test Circuit

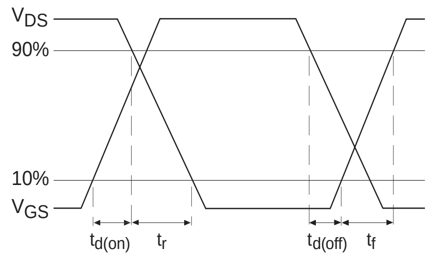


Fig 10b. Switching Time Waveforms

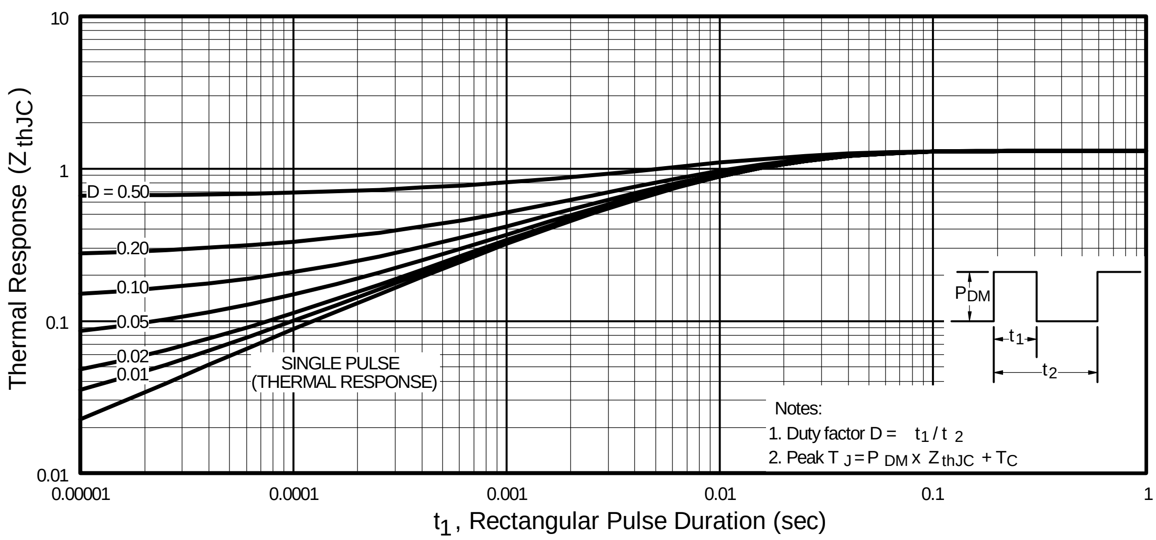


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

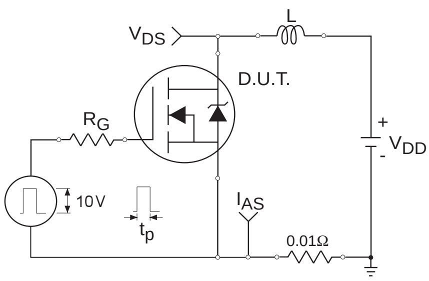


Fig 12a. Unclamped Inductive Test Circuit

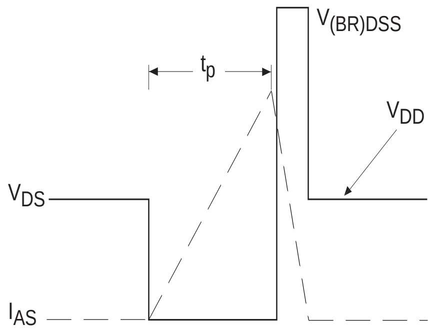


Fig 12b. Unclamped Inductive Waveforms

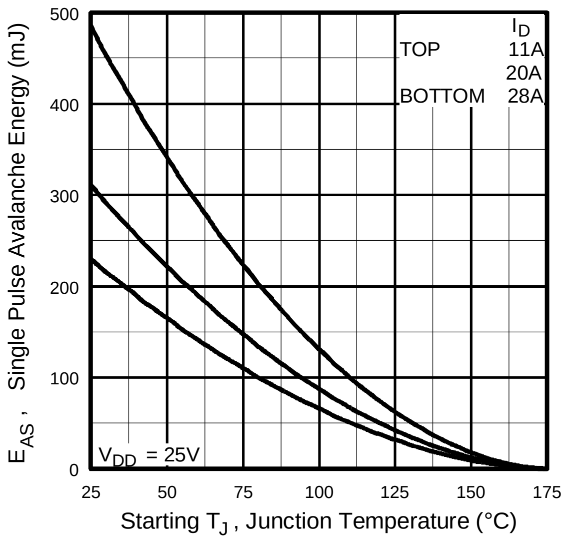


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

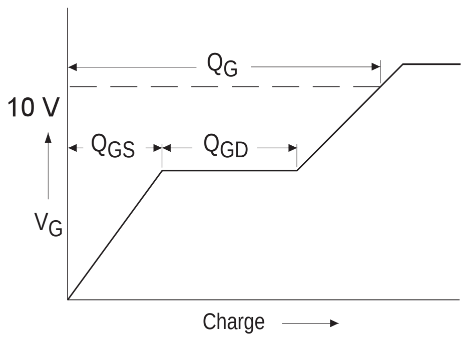


Fig 13a. Basic Gate Charge Waveform

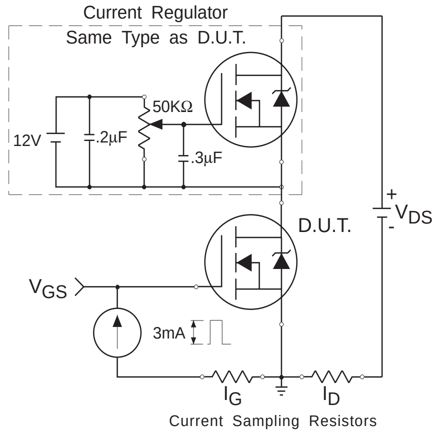
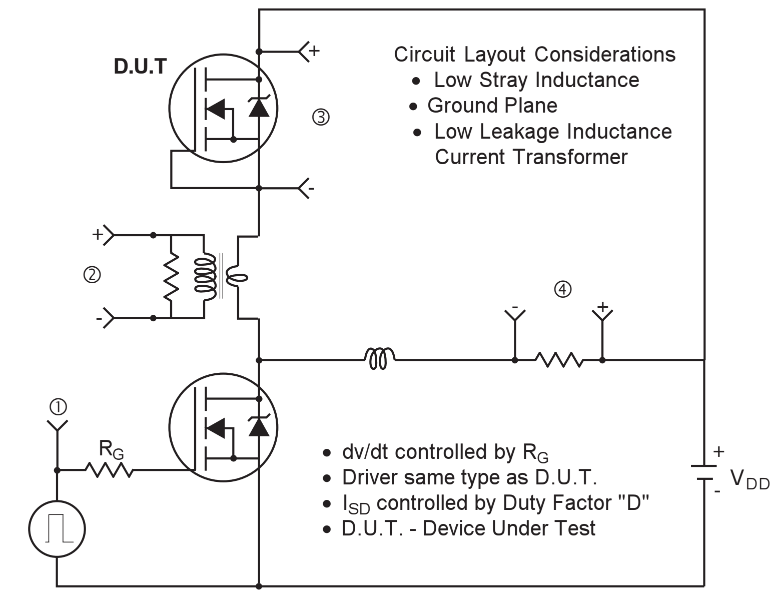
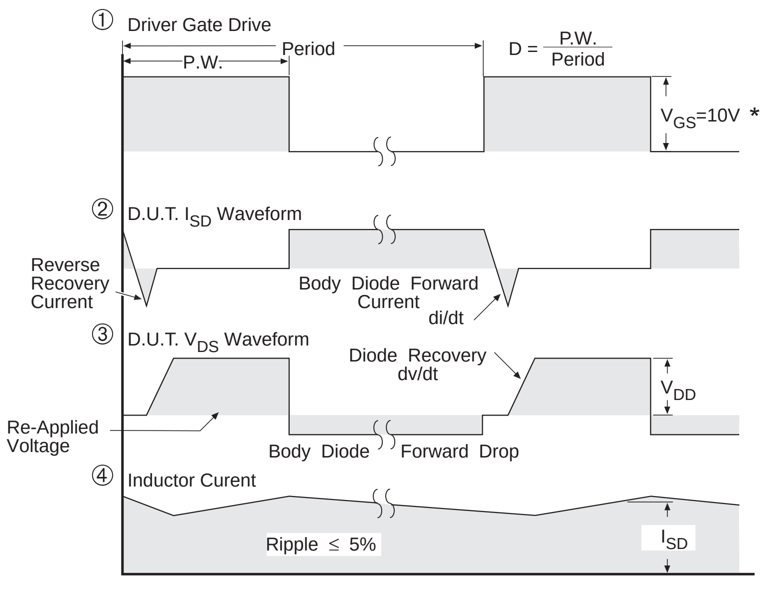


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit

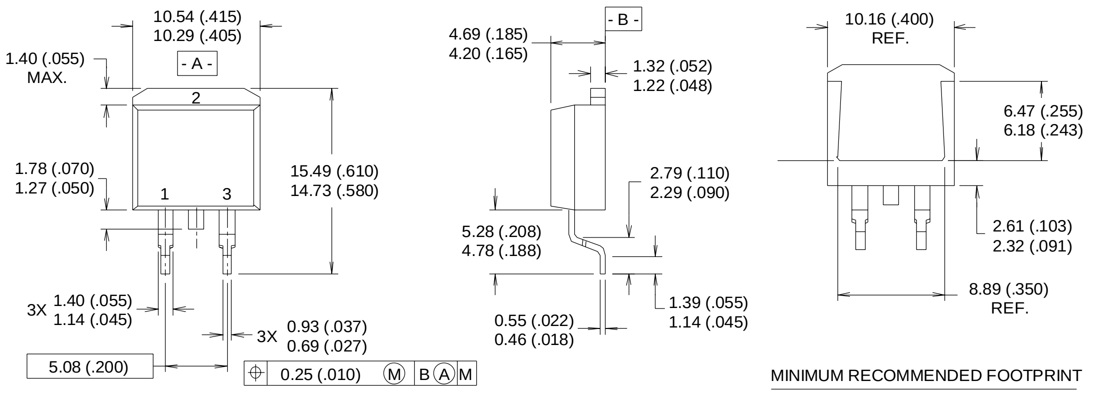




* V_{GS} = 5V for Logic Level Devices

Fig 14. For N-Channel HEXFETS

D²Pak Package Outline

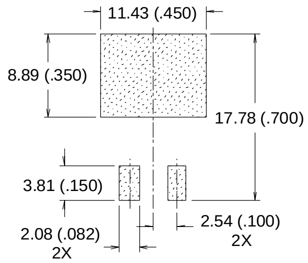


NOTES:

1. DIMENSIONS AFTER SOLDER DIP.
2. DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
3. CONTROLLING DIMENSION : INCH.
4. HEATSINK & LEAD DIMENSIONS DO NOT INCLUDE BURRS.

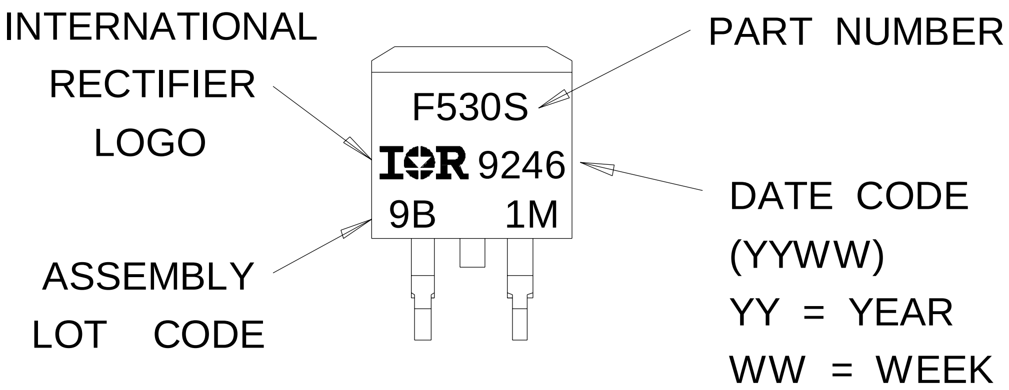
LEAD ASSIGNMENTS
1 - GATE
2 - DRAIN
3 - SOURCE

MINIMUM RECOMMENDED FOOTPRINT



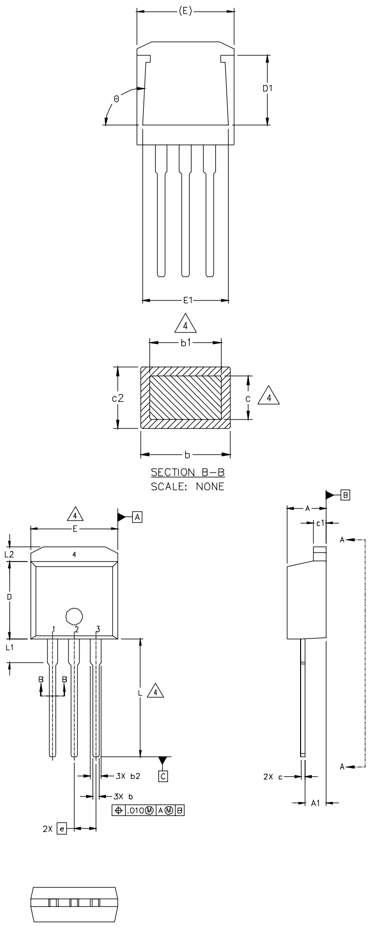
Part Marking Information

D²Pak



TO-262 Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

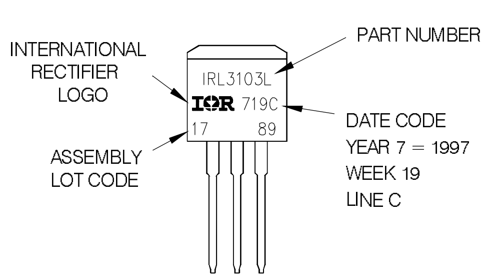
LEAD ASSIGNMENTS

HEXFET	IGBT
1.– GATE	1- GATE
2.– DRAIN	2- COLLECTOR
3.– SOURCE	3- EMITTER
4.– DRAIN	

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

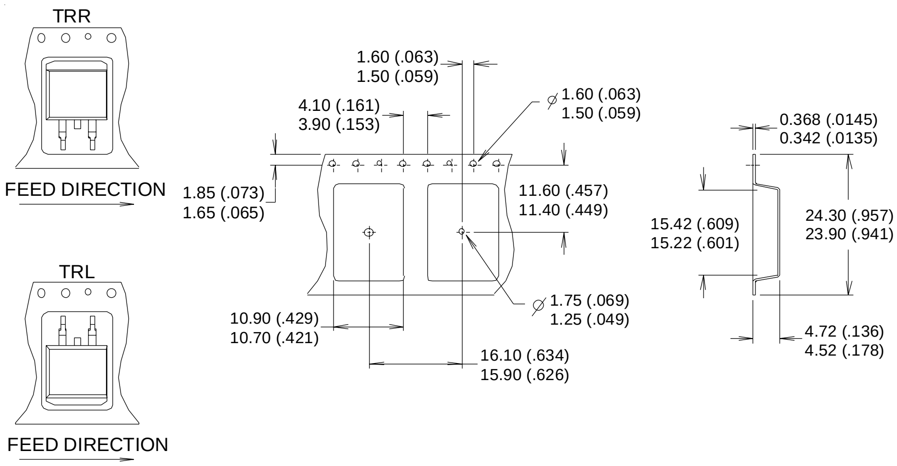
TO-262 Part Marking Information

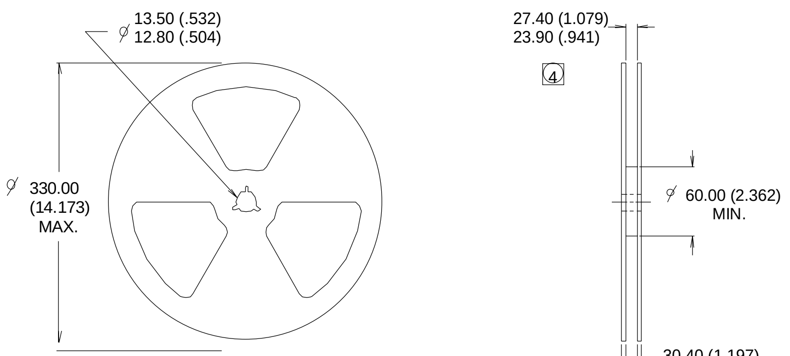
EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



Tape & Reel Information

D²Pak





NOTES :
1. COMFORMS TO EIA-418.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION MEASURED @ HUB.
4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Data and specifications subject to change without notice.
This product has been designed and qualified for the industrial market.
Qualification Standards can be found on IR's Web site.

International
IOR Rectifier

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